

Features

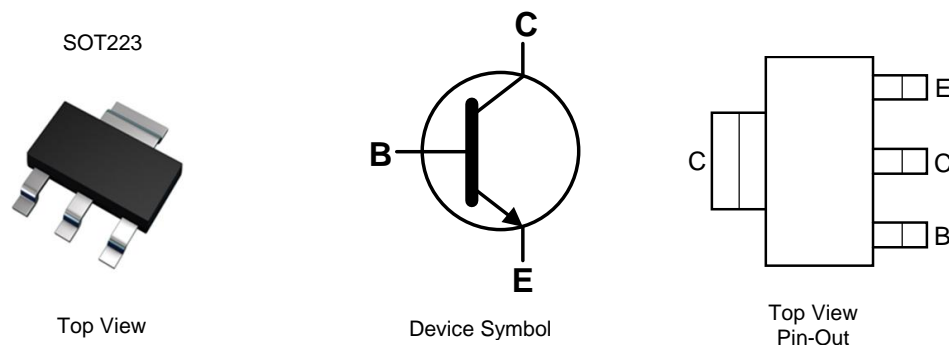
- $BV_{CEX} > 100V$
- $BV_{CEO} > 20V$
- $BV_{ECO} > 6V$
- $I_C = 7A$ High Continuous Current
- Low Saturation Voltage $V_{CE(sat)} < 48mV @ 1A$
- $R_{CE(sat)} = 31m\Omega$
- Complementary PNP Type: ZXTP25020DG
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 $\text{\textcircled{3}}$
- Weight: 0.112 grams (Approximate)

Applications

- DC-DC Converters
- Motor Drive
- Relay, Lamp and Solenoid Drive
- Regulator Circuits

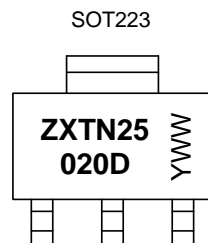


Ordering Information (Notes 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25020DGTA	AEC-Q101	ZXTN25020D	7	12	1,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



ZXTN25020D = Product Type Marking Code
 YWW = Date Code Marking
 Y or \bar{Y} = Last Digit of Year (ex: 5= 2015)
 WW or $\bar{W}W$ = Week Code (01~53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage (forward blocking)	V _{CEX}	100	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Collector Voltage (reverse blocking)	V _{ECO}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	7	A
Base Current	I _B	1	A
Peak Pulse Current	I _{CM}	15	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

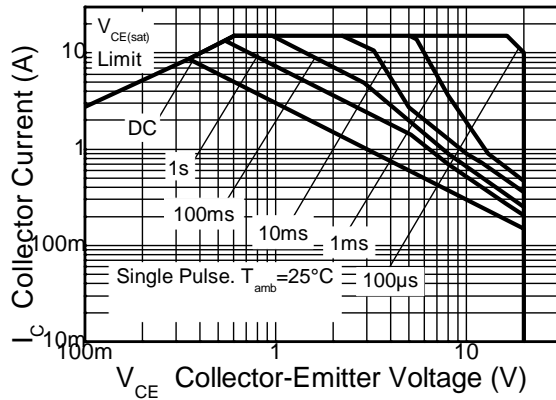
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P _D	1.2	W mW/°C
		9.6	
		1.6	
		12.8	
		3	
Thermal Resistance, Junction to Ambient	R _{θJA}	24	°C/W
		5.3	
		42	
		104	
Thermal Resistance, Junction to Lead	R _{θJL}	78	°C/W
		42	
		23.5	
Thermal Resistance, Junction to Solder Point	R _{θJS}	16	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 10)

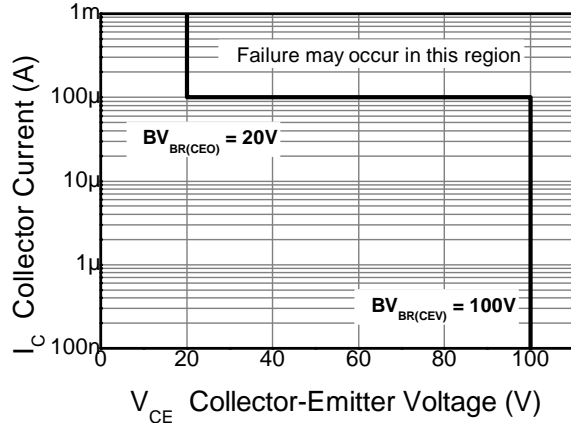
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 - Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 - Same as Note 7 measured at t<5 seconds.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

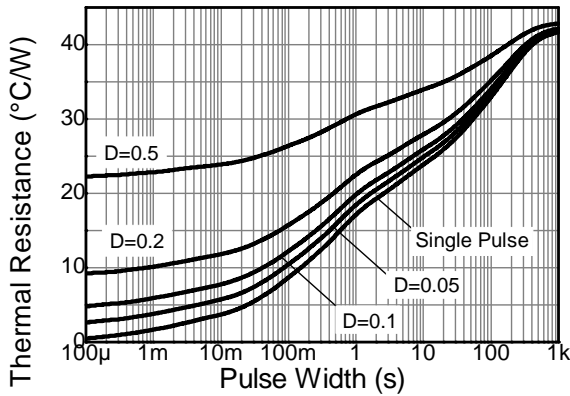
Thermal Characteristics and Derating Information (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



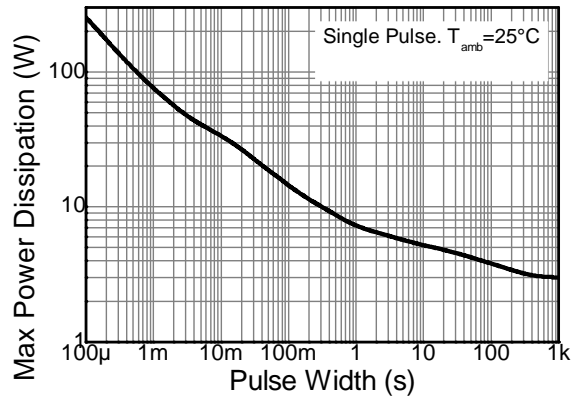
Safe Operating Area



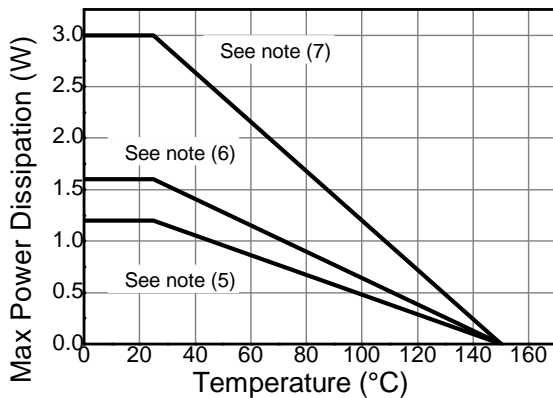
Safe Operating Area



Transient Thermal Impedance



Pulse Power Dissipation



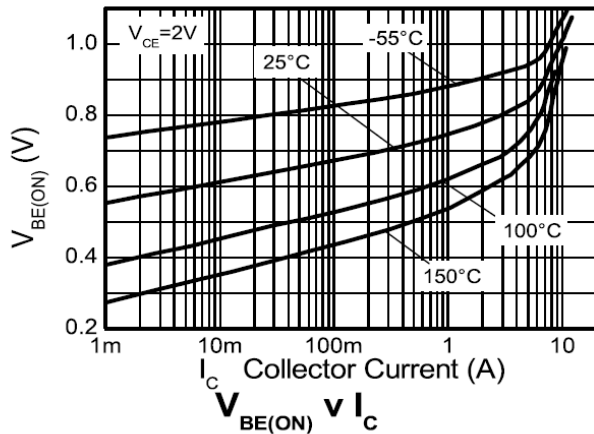
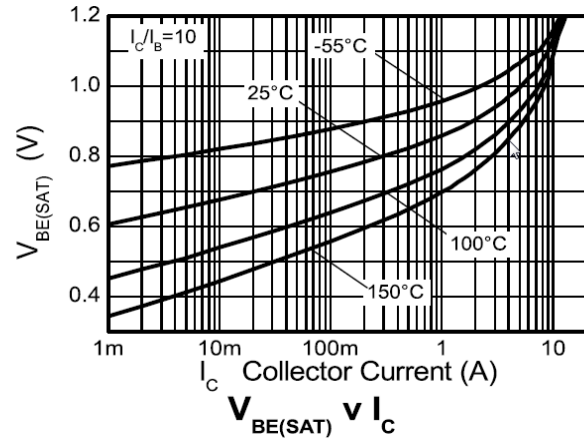
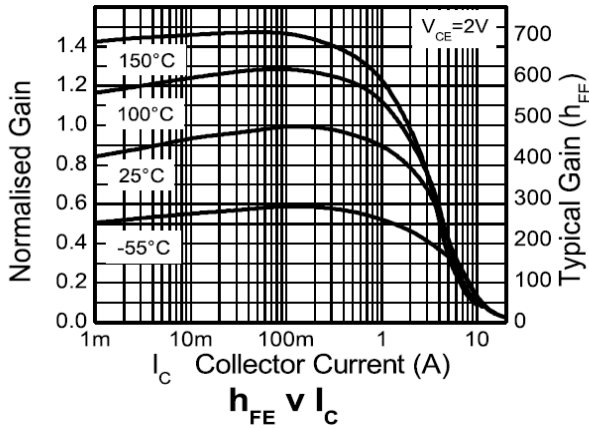
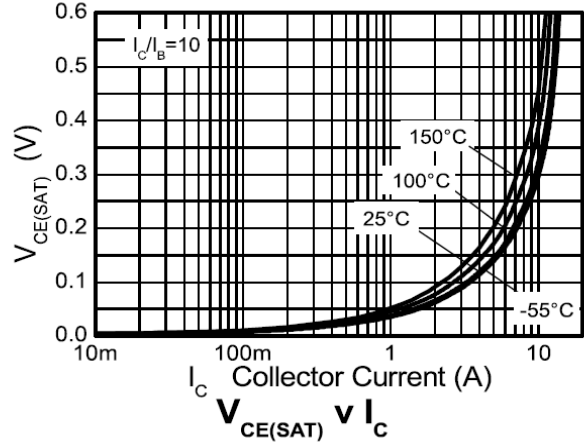
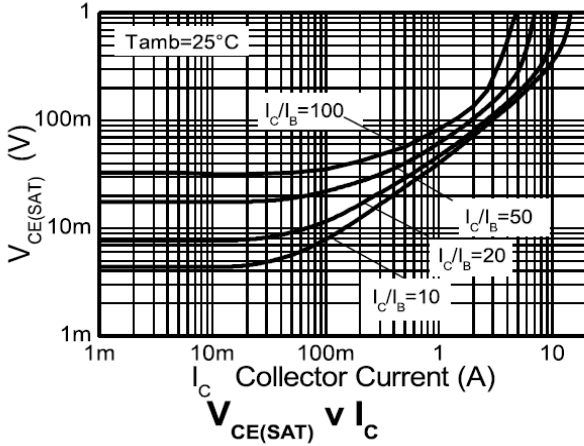
Derating Curve

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	100	125	–	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (forward blocking)	BV _{CEX}	100	120	–	V	I _C = 100μA, R _{BE} <1kΩ or -1V < V _{BE} > 0.25V
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	20	35	–	V	I _C = 10mA
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECX}	6	8.3	–	V	I _E = 100μA, R _{BC} <1kΩ or 0.25V < V _{BC} > -0.25V
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECO}	5	6.1	–	V	I _E = 100μA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	–	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	–	< 1	50	nA	V _{CB} = 100V
		–	–	0.5	μA	V _{CB} = 100V, T _A = 100°C
Collector-Emitter Cut-Off Current	I _{CEX}	–	–	100	nA	V _{CE} = 100V, R _{BE} <1kΩ or -1V < V _{BE} > 0.25V
Emitter Cut-Off Current	I _{EBO}	–	< 1	50	nA	V _{EB} = 5.6V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	–	40	48	mV	I _C = 1A, I _B = 100mA
		–	60	75	mV	I _C = 1A, I _B = 20mA
		–	100	120	mV	I _C = 2A, I _B = 40mA
		–	130	180	mV	I _C = 2A, I _B = 20mA
		–	225	290	mV	I _C = 7A, I _B = 700mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	–	1,090	1,150	mV	I _C = 7A, I _B = 700mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	–	950	1,050	mV	I _C = 7A, V _{CE} = 2V
DC Current Gain (Note 11)	h _{FE}	300	450	900	–	I _C = 10mA, V _{CE} = 2V
		250	360	–	–	I _C = 2A, V _{CE} = 2V
		50	85	–	–	I _C = 7A, V _{CE} = 2V
		–	15	–	–	I _C = 15A, V _{CE} = 2V
Current Gain-Bandwidth Product (Note 11)	f _T	–	215	–	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Input Capacitance (Note 11)	C _{ibo}	–	152	–	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance (Note 11)	C _{obo}	–	16.5	25	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _d	–	67.7	–	ns	I _C = 1A, V _{CC} = 10V, I _{B1} = -I _{B2} = 10mA
Rise Time	t _r	–	72.2	–	ns	
Storage Time	t _s	–	361	–	ns	
Fall Time	t _f	–	63.9	–	ns	

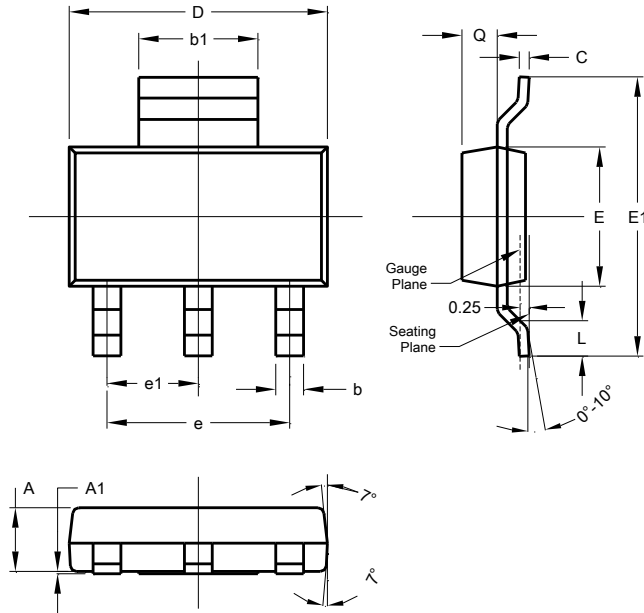
Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

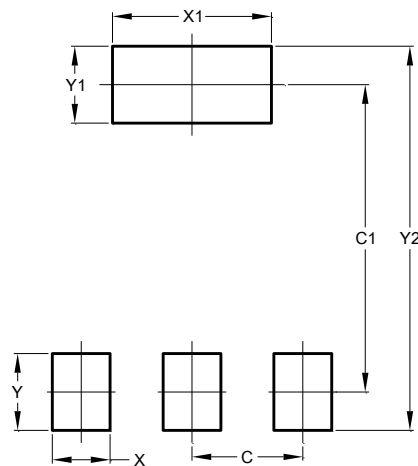
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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